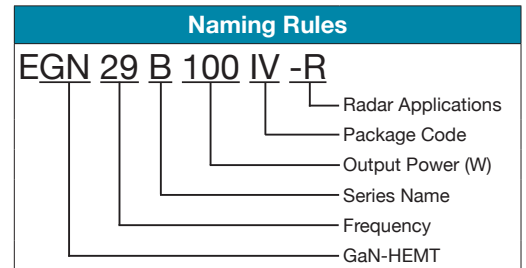


GaN HEMTs (High Electron Mobility Transistors)

For Radar

Features

- Designed for L-band / S-band Radar Applications
- Higher Impedance for Ease of Use
- Broadband Operation: 200MHz for L-band, 400MHz for S-band
- High Operating Voltage: 50V
- High Power: Up to 400W
- High Efficiency: 50%
- High Gain
- Low Thermal Resistance (Rth)



Specifications

Part Number	Frequency (GHz)	Pout min. (W)	Power Gain min. (dB)	Efficiency Typ. (%)	VDS (V)	IDS (DC) (mA)	Outline/ Package Code
EGN13B200IV-R	1.2-1.4	170	16.3	55	50	1000	IV
EGN28B100IV-R	2.7-2.9	120	12.8	56	50	500	
EGN28B200IV-R	2.7-2.9	230	12.6	53	50	1000	
EGN28B400M1B-R	2.7-2.9	400	12	50	50	2000	M1B
EGN29B100IV-R	2.7-3.1	100	12	56	50	500	IV
EGN29B200IV-R	2.7-3.1	200	11	53	50	1000	
EGN31B100IV-R	2.9-3.3	120	11.8	55	50	500	
EGN31B200IV-R	2.9-3.3	200	11	50	50	1000	
EGN33B100IV-R	3.1-3.5	100	11	50	50	500	

Specifications (Driver Stage)

Part Number	Frequency (GHz)	P3dB min. (dBm)	GL min. (dB)	η @P3dB Typ. (%)	VDS (V)	IDS (DC) (mA)	Outline/ Package Code
EGNB010MK	3.5	40	12	60	50	100	MK
EGN31B030MK	3.1	45.5	12	45	50	200	

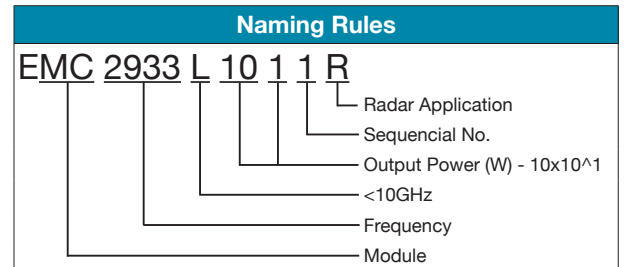
GaN HEMT Pallet Amplifiers for Radar

Features

- Designed for S-band Radar Applications
- 50 ohm matched
- Broadband Operation: 400MHz
- High Operating Voltage: 50V
- High Power: Up to 200W
- High Efficiency: 50%
- High Gain
- RC Bias Circuits included
- Copper Base

Specifications

Part Number	Frequency (GHz)	Pout min. (W)	Power Gain min. (dB)	Efficiency Typ. (%)	VDS (V)	IDS (DC) (mA)	Outline/ Package Code
EMC2933L1011R	2.9-3.3	120	11.8	55	50	500	Pallet-S
EMC2933L2011R	2.9-3.3	200	11	50	50	1000	
EMC3135L1011R	3.1-3.5	100	11	50	50	500	



Package Photo

